Toward one-band superconductivity in M gB₂

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The two-gap model for superconductivity in M gB₂ predicts that interband impurity scattering should be pair breaking, reducing the critical temperature. This is perhaps the only prediction of the model that has not been con m ed experim entally. It was previously shown theoretically that com m on substitutional impurities lead to negligible interband scattering if the lattice is assumed not to distort. Here we report theoretical results showing that certain impurities can indeed produce lattice distortions su ciently large to create measurable interband scattering. On this basis, we predict that isoelectronic codoping with Al and Na will provide a decisive test of the two-gap m odel.

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It is now widely accepted that M gB₂ is a two-gap superconductor: its Ferm i surface consists of two distinct sheets characterized by strong and weak electron-phonon coupling, respectively (see R ef. 1 for a review). This view is supported by num erous experim ents probing either the larger or sm aller gap, or both simultaneously. Experim ental observation of the m erging of the two gaps would constitute even stronger evidence. Such a m erging is expected, for example, from interband scattering by in purities. W ithin the theory of multiband superconductivity, interband scattering m ixes the \weak" and \strong" Cooper pairs, averaging the order param eter and reducing T_c [2]. At sm all defect concentrations the suppression ofTc should be linear, with the larger gap decreasing and the smaller gap increasing. The e ect should be pronounced in samples with high defect concentrations, but despite the relatively low quality of many samples such an e ect has not been observed. Indeed, som e sam ples with high resistivity have nearly the same critical tem peratures as clean single crystals. On the other hand, samples doped with carbon show both gaps decreasing but not m erging, despite a considerable reduction in T_c . O ther types of intentional defects whether from doping or irradiation have also failed to produce a m erged gap. Even e orts to introduce defects into $M gB_2$ for the explicit purpose of inducing interband scattering and merging the two gaps have failed to observe this e ect [3, 4, 5, 6].

This apparent lack of evidence for a central prediction of the two-gap model is disturbing. In Ref. [7] it was shown that interband scattering from substitutional in – purities is inherently weak, if the lattice is assumed not to distort. This partially explains the null results of current experimental e orts to induce pair breaking, but it does not address the possibility of pair breaking from in purities speci cally chosen to maxim ize the interband scattering due to large lattice distortions. In this Letter we show that this strategy is likely to succeed and, by identifying a simple relationship between in purity atom s and the resulting lattice distortions in M gB₂, suggest an im purity-doping protocol that will produce measurable pair breaking | and thereby provide the nal \sm okinggun" evidence for the two-band model.

Ham pering such investigations is the currently lim ited insight into which defects are most e ective in creating interband scattering. Since the states at the Ferm i level of M gB_2 are form ed by the boron orbitals, one m ight expect in purities (such as carbon) in the B planes to produce large interband scattering. This is not borne out experim entally: substitutional C im purities have only a weak e ect on the interband scattering [5]. This nding had been anticipated theoretically as a consequence of the special symmetry properties of the electronic states within the band near the point [7]. The crucial point is that although in purities in the B plane do have a strong e ect on the electronic structure, they do not change the local point symmetry and therefore do not lead to signi cant scattering.

The situation can be quite di erent for substitutions in the M g plane, which m ay create out-of-plane distortions of B atom s in neighboring planes. Such relaxations do change the local point sym metry of nearby B atom s, m ixing the in-plane $p_{x,y}$ and out-of-plane p_z orbitals, and for su ciently large disturbances can lead to signi cant

scattering. Here we demonstrate by rst-principles calculations that this is indeed the case for certain substitutional impurities but | surprisingly | not for M g vacancies. W e predict that the interband scattering e ects will be most pronounced for isoelectronic co-doping with N a and A l, and that the e ect on the superconducting properties should be detectable for impurity concentrations above 2%.

W e used density-functional theory (DFT) to study the lattice distortion created by M g-plane substitutional in – purities from G roups I, II, and III, by a M g vacancy, and by B-plane C substitution. To model the distortion induced by single defects, we used 2 2 2 supercells of bulk M gB₂ (and 3 3 3 supercells for convergence checks). Total energies and forces were calculated using projector-augmented-wave potentials and the generalized-gradient

2

TABLE I: First-principles displacements of nearest-neighbor B atom s, in angstrom, induced by various substitutional im – purities. Positive values indicate displacements away from the impurity.

In purity	Site	In-plane, r	0ut-of-plane, z
Be	Мg	0.014	0.039
Al	Мg	0.012	0.033
Sc	Мg	+ 0.012	0.008
С	В	+ 0.044	0
Li	Мg	0.006	+ 0.003
Vacancy	Мg	0.005	+ 0.008
Ca	Мg	+ 0.015	+ 0.028
Na	Мg	+ 0.008	+ 0.040
К	Мg	+ 0.024	+ 0.092

approximation [9, 10]. All atom ic positions were relaxed within the constraint of xed (theoretical) bulk lattice parameters. The resulting displacements of the nearestneighbor B atom s are given in Table I.G iven the strong intraplanar covalent bonding, it is not surprising that these displacements are dominated by the out-of-plane component z, which ranges from 0.04 A (for Be) to + 0.09 A (for K); for C it is zero by symmetry.

The out-ofplane displacements for seven di erent in purities on the M g site are plotted in F ig.1. In a previous related study, changes in interlayer spacing induced by the complete substitution of A l for M g in a single plane were ascribed to electrostatic e ects [11]. We nd no such correlation between z and the form alvalence of the impurity | for example, Be and C a give displacements of opposite sign despite having identical valence | and thus infer that electrostatic e ects are not in portant. On the other hand, F ig. 1 shows that there is an excellent correlation between z and the ionic radius of the impurity atom . Hence, we conclude that the out-of-plane displacement of B atom s by impurity atom s substituting for M g is mostly a size e ect.

In light of this, one m ight anticipate a M g vacancy to produce a large inward displacement. Our DFT results reveal very di erent behavior: the vacancy creates a negligibly small displacement, z < 0.01 A. This result is consistent with the experimental fact that pair breaking is not observed in low quality samples, which presumably contain m any vacancies. How ever, it is very di erent from the trend shown in Fig. 1. Indeed, if one naively considers the vacancy as an impurity of zero size, the predicted displacement is alm ost twice that found for Be and Al, in sharp distinction to our DFT result.

A simple model explains the surprisingly small displacement created by the Mg vacancy. We consider a MgB₂ crystal containing a single substitutional defect D (either an impurity atom or a vacancy) in the Mg plane. Such a defect has 12 nearest-neighborB atom s, consisting



FIG.1: First-principles theoretical displacements of nearestneighbor B atom s around a substitutional impurity in the M g plane. Ionic radii are from Ref. 8.

oftwo hexagonal rings. W e consider the out-of-plane displacem ent of the B atom s in these rings to arise from two opposing e ects. The rst of these represents the change in covalent bonding between B planes. In the absence of any defects, the M gB₂ interlayer spacing q_{Mq} is prim arily determ ined by assisted hopping between B p_z orbitals through Mg orbitals; for each B atom there are three such hopping paths through nearest-neighbor M g atom s. W ith the defect present, one of these three paths now passes through the defect site. This new hopping path results in an out-of-plane force on the B atom . W e assum e the magnitude of this e ect to be one-third of that found for a fully substituted M g plane, which we approxin ate using the energy vs. layer spacing, E_D (c), for fully substituted DB2. Thus, we consider the change in spacing between the two displaced hexagonal rings, 2 z, to contribute an energy per B given by $\frac{1}{3}E_D$ (q_{Mg} + 2 z). W e have calculated the binding-energy curves E_D (c) within DFT for $A \mathbb{B}_2$, $N \otimes B_2$, and $\vee =$ substituted \mathbb{B}_2 ; the results are shown in Fig. 2. All can be accurately represented by a M orse potential, which is the form we will use in the discussion below .

The second e ect is the restoring force experienced by the displaced B atom s, due to the strong covalent bonding within the B planes. For the sm all displacements we are considering it is reasonable to take this e ect to be harm onic in z, again weighted by 1/3. Thus we take the total energy change per B to be

E (z) =
$$\frac{1}{3}K$$
 (z)² + $\frac{1}{3}kw^{2}$ [1 e $(Q_{M_{g}}+2z_{O})=w$]²; (1)

where w is the width of the M orse potential, kw^2 its depth, and q_b its equilibrium interlayer spacing. For small $q_{M g} = q_b$, it is easy to show that this energy is minimized for $2 z = (q_b = q_{M g}) = (1 + K = 2k)$. In other

words, for in purities whose size is comparable to M g, the displacement is linear in the size m ismatch and reduced by the factor 1 + K = 2k (which is typically in the range 5(10); this is consistent with the DFT results shown in Fig. 1. Qualitatively, when $c_{\rm D}$ is close to $q_{\rm Mg}$, as it is for A B₂ and N aB₂, the equilibrium displacement represents a balance between the harmonic restoring force $\frac{2}{3}K$ j z j and a nearly harmonic (attractive or repulsive) force $\frac{2}{2}k(q_{\rm Mg} - q_{\rm D} + 2 z)$ from the interlayer bonding.

For the vacancy there is a very large size m ism atch: c_{vac} is over 40% sm aller than q_{Mg} . Thus for any reasonable displacement, the hexagons experience only a weak attractive force from the tailof the M orse potential. Hence, the energy ism inim ized for a very sm all displacement, z 0:007 A, in agreement with the negligible displacement given by DFT. Qualitatively, the result of a large size m ism atch is to largely preempt the mechanism of interlayer binding, leading to very sm all displacements strongly suppressed by the penalty for perturbing the planarity of the B layer.

The origin of the large m ism atch between $q_{M,q}$ and c_{vac} . can best be understood by comparing the band structures of the fully substituted DB₂ compounds at their equilibrium interlayer spacings. For these pure com pounds (as well as the parent m aterial) interlayer bonding arises primarily from the interaction between B pz orbitals in di erent layers. This interaction depends on the assisted hopping through s and pz orbitals located on the D site. However, for the fully \vacancy substituted" compound the occupancy of the bands is so much reduced that their contribution to bonding becom es quite small. At the same time, the bands acquire substantial z-dispersion from pp hopping, which contributes to bonding. Even for high vacancy concentrations (without com plete rem oval of a M g plane) it is impossible to engage the bands in interlayer bonding by any reasonable dim pling of the B planes, because the planes rem ain too far apart. As a result, hardly any distortion occurs at all: indeed, even for 50% vacancies within a single M g plane, the interlayer spacing changes by less than 0.05 A.

We have established that the defects leading to the largest B displacements are Mg-plane substitutional im purities with a large size m ism atch (but not Mg vacancies). We now estimate the magnitude of the interband scattering associated with displacements from such im purities. We assume that the only relevant scattering is that due to the out-of-plane distortion, z, and use the analogy between the form ulas [12] for the impurity-induced scattering rate,

$$_{im p} = n_{im p} \frac{\sum_{k k^{0}} (\mathbf{I}_{k}) (\mathbf{I}_{k^{0}}) j V_{k k^{0}}}{\sum_{k} (\mathbf{I}_{k})}; \qquad (2)$$

and the electron-phonon coupling constant,

D

$$= \frac{\sum_{jkk^{0}}^{P} (\mathbf{I}_{k}^{n}) p_{jkk^{0}} p_{jkk^{0}}}{p_{k}} = h! ;_{k k^{0}} p_{jkk^{0}} p_{j$$



FIG. 2: First-principles cohesive energy of completely substituted M gB_2 , versus interlayer spacing. Curves are ts to M orse potentials. The vertical dotted line m arks the equilibrium interlayer spacing for M gB_2 .

Here $n_{im p}$ is the impurity concentration; V_{kk^0} is the matrix element of the impurity perturbation potential (de ned as the di erence between the full crystal potentials with and without an impurity); "k is the electron energy with respect to the Fermi level; ! k is the phonon frequency; $M_{k;k^0}$ is the electron-ion matrix element k $jV=dQ_k^0$, where dV=dQ is the derivative of the crystal potential with respect to the phonon normal coordinate $Q = \sum_{m=1}^{N} 2m! = hx$; and the sum mations are over all electron states and all phonon branches [12].

To proceed we make three approximations, all qualitatively reasonable if not quantitatively reliable. First, we assume that in-plane phonons, including the well-known E_{2g} modes, contribute little to interband electron-phonon coupling; this follows from the same symmetry arguments given in Ref. 7. Second, we assume by the same reasoning that interband in purity scattering comes only from the out-of-plane relaxation of B atoms. Finally, we approximate Eq.2 as

$$\begin{array}{c} X & \stackrel{!}{D} & E \\ \lim_{m p} 12 & n_{im p} & ("_k) & jdV = du_z \\ k & \\ & k \end{array}$$

and likew is Eq.3 as

$$\begin{array}{cccc} X & {}^{!} D & E \\ 2 & ({}^{"}_{k}) & j dV = du_{z} \\ {}^{j}_{k} & \end{array} = 2m \; {}^{2} : \qquad (5)$$

Here we have assumed that the average of the crystal potential with respect to the vertical displacement of the B atom is the same in both cases. The numerical factors 12 and 2 are the coordination of M g and the number of B atom s in the unit cell, respectively.

F irst-principles calculations give the interband part of the electron-phonon coupling as 0.2 [1]. The phonon frequencies for the out-of-plane modes are about 400 am¹: U sing these values, the scattering rate is given by $\lim_{m p} 50 n_{im p} (z)^2 eV$, where z is in angstrom. Hence, for 2% Aldoping we nd imp 1:1 m eV.For 2% Nadoping we estim ate a sim ilar scattering rate, imp 1:3 m eV. These scattering rates are sm all, but should still have a m easurable e ect on the superconducting gaps and tem perature. The e ect on the gaps is di cult to estimate without full Eliashberg calculations. The reduction of T_c can be easily estimated using Eq. 13 from Ref. [2], which gives 2.0{2.5 K (in addition to any suppression due to the electron doping of the band). W hile this is a small reduction compared to the changes observed in heavily electron-doped sam ples, the underlying m echanism is quite di erent. In particular, pair breaking from interband scattering is unique in that it reduces T_c and the gap ratio while simultaneously increasing the smaller gap [2]. This distinctive behavior should facilitate the separation of interband scattering from other sources of T_{c} reduction.

Finally, we suggest that an especially attractive test of these predictions would be simultaneous codoping by equal parts A l and N a. This would e ectively be an isoelectronic substitution, and any e ect on the superconducting properties could then be ascribed to impurityinduced interband scattering. Moreover, N a and A l induce distortions of the same magnitude but of the opposite sign, which should mitigate the e ects of a reduction in scattering due to possible short-range ordering of the impurities.

In conclusion, we have performed rst-principles calculations of the lattice distortion in M gB₂ induced by several common substitutional (for M g) in purities, and a M g vacancy. We nd out-of-plane displacements as large as 0.04 A for common in purities such as A land N a. The m agnitude and sign of the displacement are mainly determ ined by the ionic size of the in purity. On the other hand, for the M g vacancy we nd an essentially negligible displacement of nearby B atom s. The dierent behavior of vacancies and in purities is explained by a simple physical model representing the competition between interlayer binding and intralayer planarity. We estimate the interband scattering rate due to the Na and Alim – purities to be of order 1 m eV, su ciently large to give a detectable change in the superconducting transition tem – perature. Finally, we propose that the codoped material Mg₁ $_{\rm X}$ N a_xA $_{\rm k}$ B₂, which is isoelectronic with MgB₂, should provide an excellent test of these predictions.

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